

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S33	20	(US-20020094686-\$ or US-20030118731-\$ or US-20040135217-\$ or US-20040048491-\$ or US-20040129294-\$ or US-20040118805-\$ or US-20040026374-\$ or US-20040089536-\$ or US-20050215059-\$ or US-20020096512-\$).did. or (US-6565667-\$ or US-6613603-\$ or US-4842897-\$ or US-6063142-\$ or US-6812101-\$ or US-6787440-\$ or US-6465371-\$ or US-6861101-\$).did. or (JP-2003203906-\$ or JP-05082165-\$).did. or (US-20030129772-A-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/11/10 15:46
S34	389100	S33 and (silicon) or (silicon near2 \$2oxide\$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/10 15:48
S35	13	S33 and ((silicon) or (silicon near2 \$2oxide\$2))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/10 15:48
S36	2	("2002/0094686").URPN.	USPAT	ADJ	ON	2008/11/10 16:08
S37	1	("20060170740").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/11/12 08:01
S38	11695	semiconductor\$2 and (silicon with dielectric)	EPO; JPO; DERWENT	ADJ	ON	2008/11/12 08:51
S39	13	semiconductor\$2 and (silicon with dielectric) and (micro near2 (fissur\$3 or crack\$3 or trench\$3 or via \$2))	EPO; JPO; DERWENT	ADJ	ON	2008/11/12 08:54
S40	1	("1158072").PN.	EPO	OR	OFF	2008/11/12 09:08

S41	2	("6783875").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/12 09:14
S44	4123	semiconductor\$2 and (("si" or silicon) same ("yt" or yttrium) same oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 09:24
S45	38	semiconductor\$2 and (("si" or silicon) same ("yt" or yttrium) same oxide) same (rough\$4 with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 09:25
S46	37	semiconductor\$2 and (("si" or silicon) same ("sio. sub."\$) same ("yt" or yttrium or "yto.sub."\$) same \$2oxide) same (rough\$4 with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 10:19
S47	94	semiconductor\$2 and (("si" or silicon) same ("y" or yttrium) same \$2oxide) same (rough\$4 with surface)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 10:25
S48	95	semiconductor\$2 and (("si" or silicon) same ("y" or yttrium) same \$2oxide) same ((rough\$4 with surface) or (micro near2 (crack\$4 or fissur\$3 or trench\$2 or via\$2)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/11/12 10:26

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